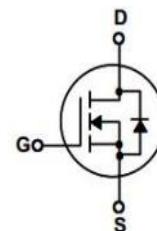
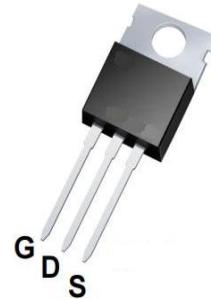




## 1. Features

- $V_{DS}$  200V
- $R_{DS(ON)} \leq 10\Omega$  @ $VGS=10V$

TO-220



1. Gate
2. Drain
3. Source

## 2. Mechanical Data

- Case:Molded Plastic,TO-220;
- Epoxy:UL 94V-0 rate flame retardant
- Terminals:Plated Leads Solderable per MIL-STD-750,Method-2026.
- Marking: marked on body.
- Mounting Position : Any.

## 3. Maximum Ratings and Electrical Characteristics

Rating at 25°C Cambient temperature unless otherwise specified

Characteristics	Symbol	Ratings	Unit
Drain-Source Voltage	$V_{DS}$	200	V
Drain Current Continuous $T_C=25^\circ C$	$I_D$	108	A
$T_C=100^\circ C$	$I_D$	74	
Drain Current Pulsed	$I_{DM}$	420	A
Single Pulsed Avalanche Energy @ $L=0.1mH$	$E_{AS}$	1332	mJ
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation( $T_C=25^\circ C$ )	$P_D$	299	W
Maximum Junction Temperature	$T_J$	-55 to +175	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 to +175	$^\circ C$
Thermal Resistance, Junction-to-Case	$R_{\theta JA}$	60	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.5	$^\circ C/W$



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Characteristics	Symbol	Test conditions	Min	TYP	Max	Unit
<b>Off Characteristics</b>						
Drain -Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200	-	-	V
Zero Gate Voltage Drain Current @ $T_J=25^\circ C$	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = 20V$	-	-	100	nA
Gate-Source Leakage Current		$V_{GS} = -20V$	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 12A$	-	8.8	10	$m\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 100V$ $V_{GS} = 0V$ $f = 1.0MHz$	-	5375	-	pF
Output Capacitance	$C_{oss}$		-	457	-	
Reverse Transfer Capacitance	$C_{rss}$		-	40	-	
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 100V, V_{GS} = 10V$ $I_D = 50A$	-	16	-	ns
Turn-on Rise Time	$t_r$		-	82	-	
Turn-off Delay Time	$t_{d(off)}$		-	55	-	
Turn-off Fall Time	$t_f$		-	84	-	
Total Gate Charge	$Q_g$	$V_{DS} = 100V, V_{GS} = 10A$ $I_D = 50A$	-	70	-	nc
Gate-Source Charge	$Q_{gs}$		-	25	-	
Gate-Drain Charge	$Q_{gd}$		-	16	-	
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$I_S = 20A, V_{GS} = 0V$	0.5	0.85	1.2	V
Reverse Recovery Time	$T_{rr}$	$I_F = 50A, V_{DS} = 0V$ $dI/dt = 100A/\mu s$	65	129	258	ns
Reverse Recovery Charge	$Q_{rr}$		376	752	1504	nC



#### 4.Rating And Characteristic Curves

Fig.1 Typical Output Characteristics

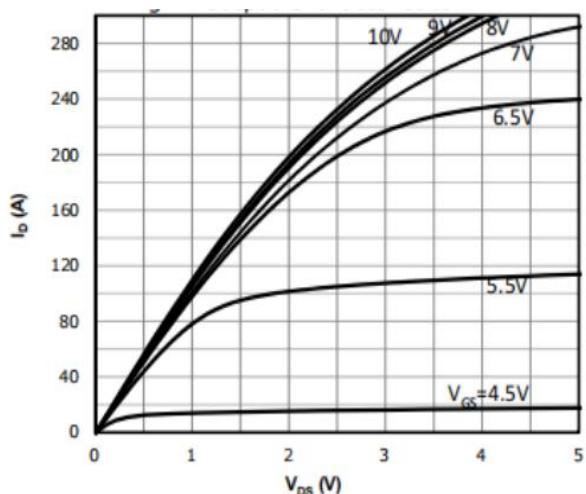


Fig.2 Transfer Characteristics

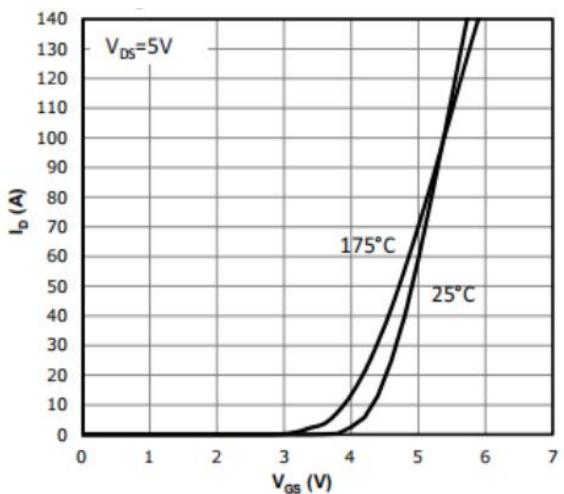


Fig.3 On-Resistance vs. Drain Current and Gate Voltage

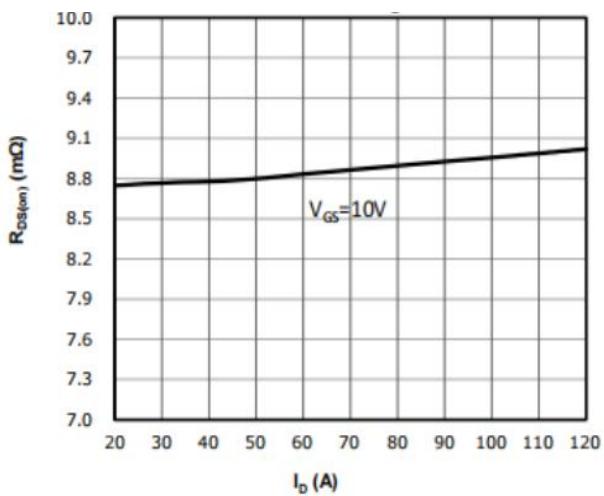


Fig.4 Rds(on) vs Gate Voltage

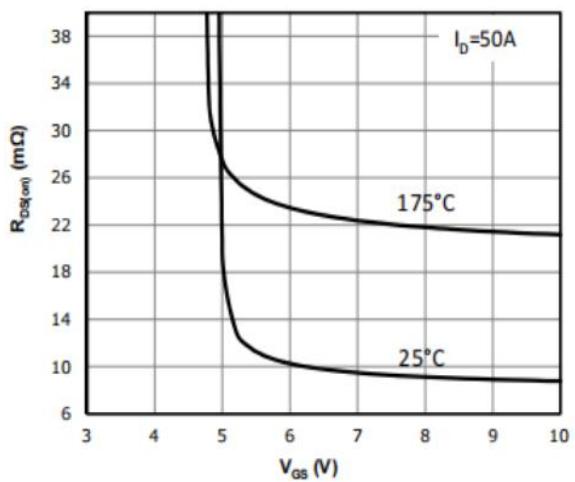


Fig.5 Rds(on) vs. Temperature

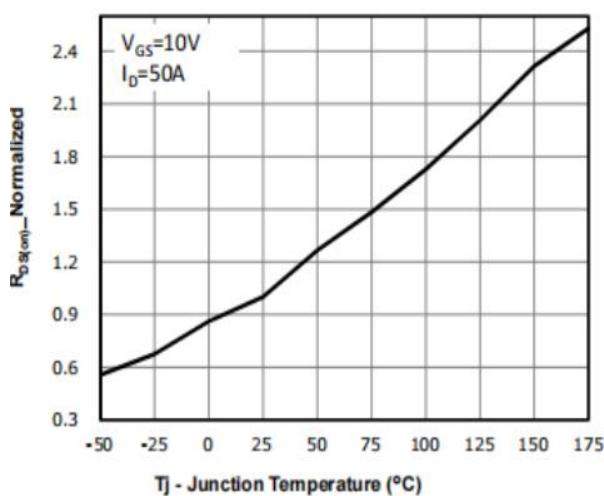
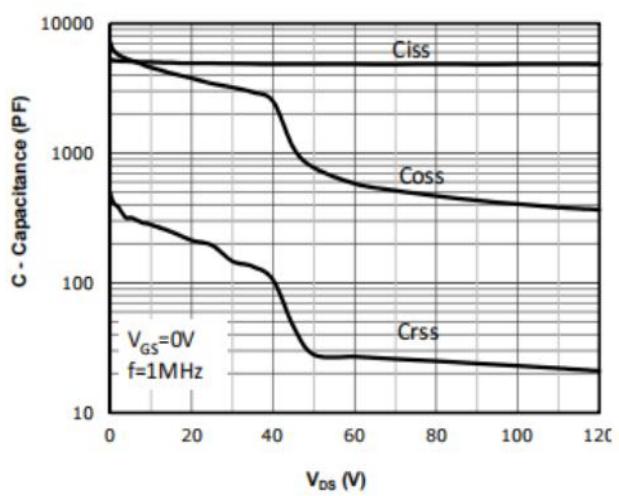


Fig.6 Capacitance Characteristics





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Fig.7 V<sub>gs(th)</sub> vs. Temperature

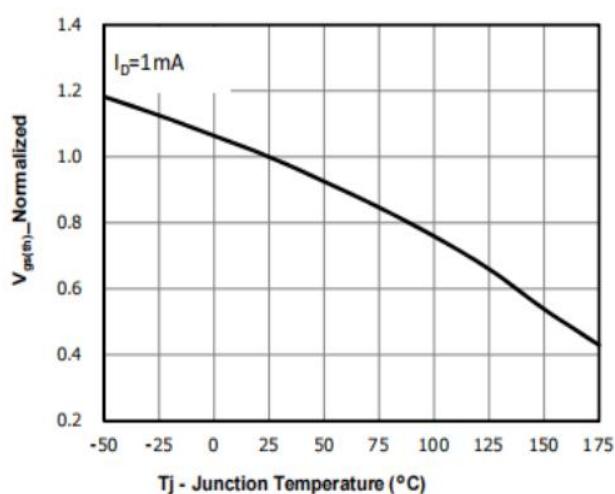


Fig.8 BV<sub>dss</sub> vs. Temperature

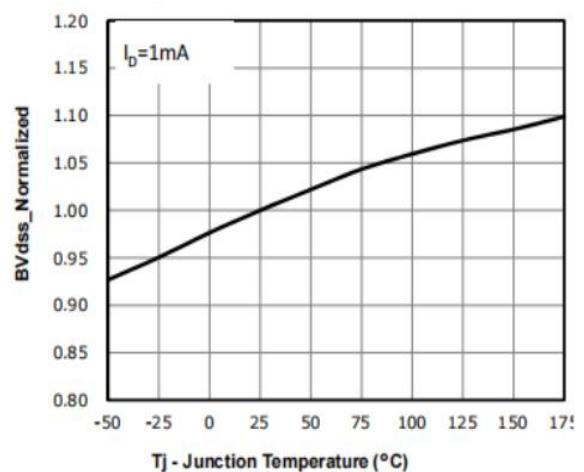


Fig.9 Gate Charge Characteristics

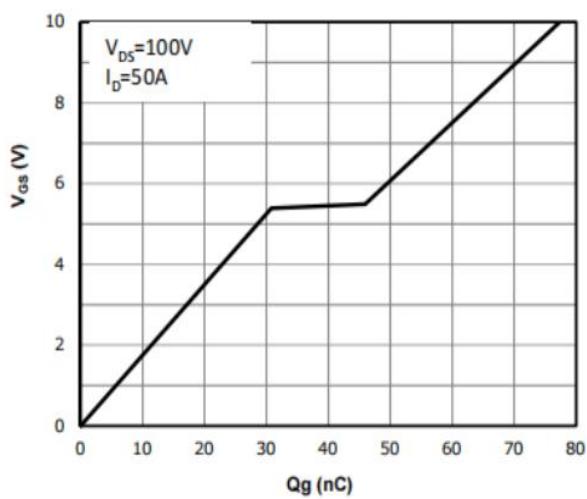


Fig.10 Body-diode ForwardCharacteristics

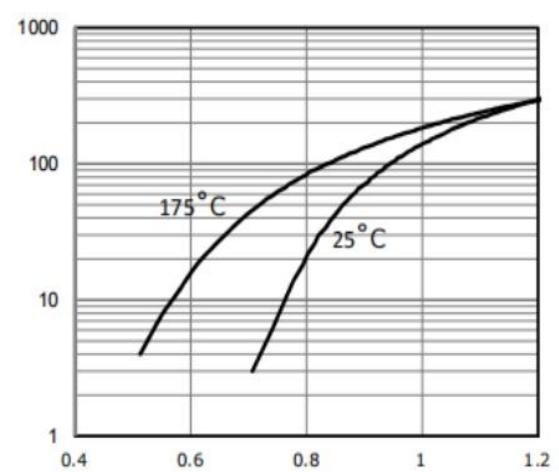


Fig.11 Power Dissipation

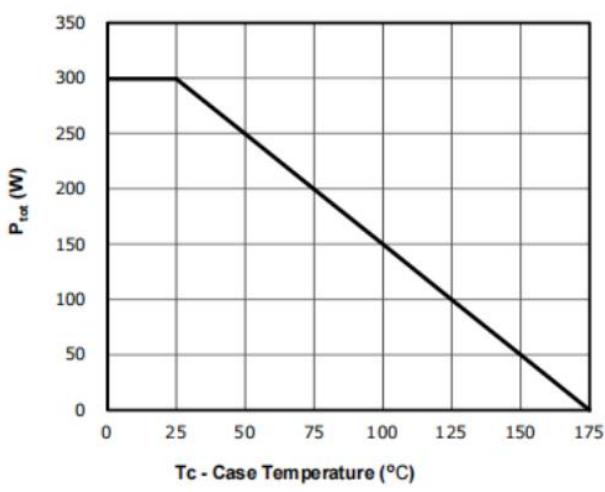


Fig.12 Drain Current Derating

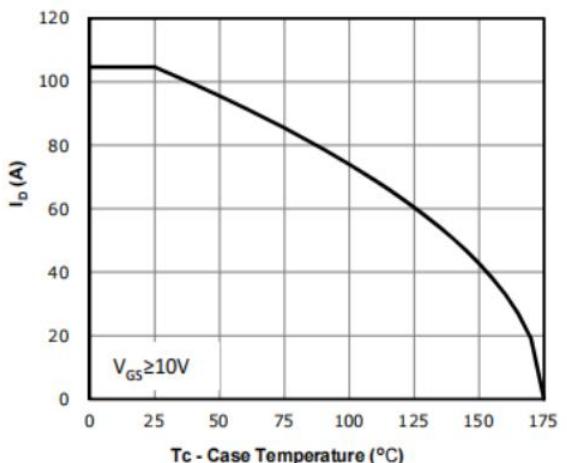




Fig.13 Safe Operating Area

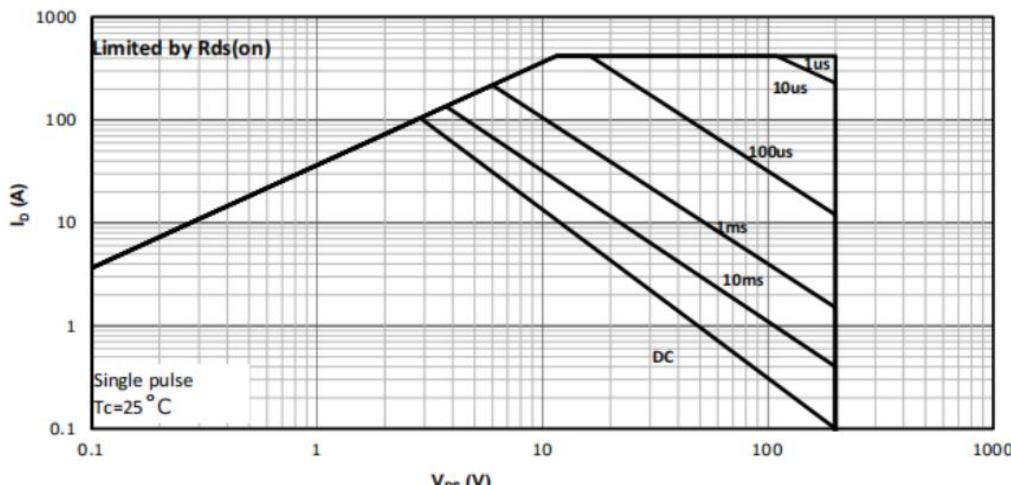
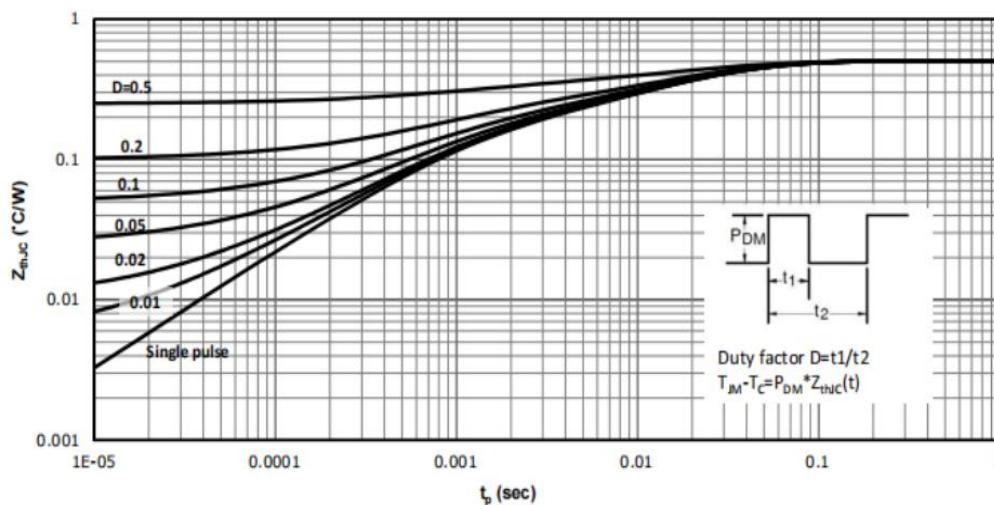


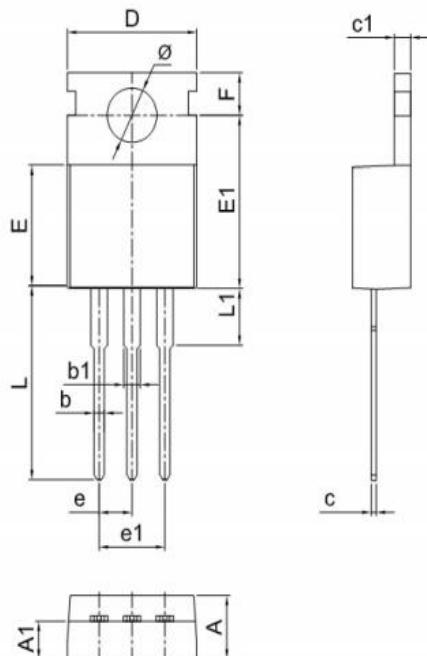
Fig.14 Max. Transient Thermal Impedance





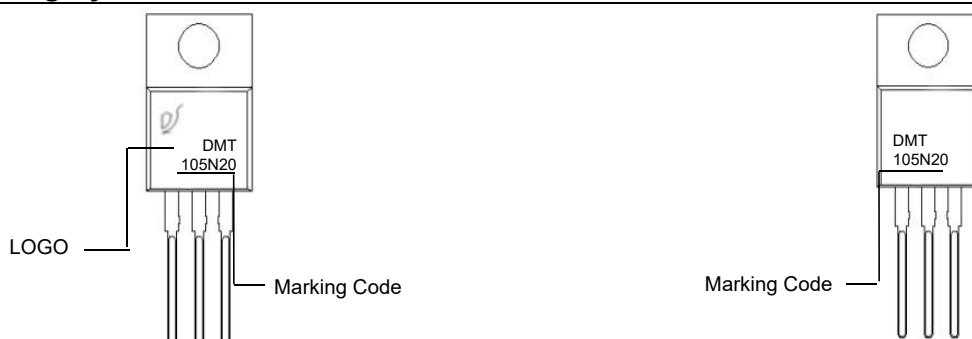
## 5. Dimensions

### TO-220 Mechanical Drawing



Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.168	0.192	4.27	4.87
b	0.016	0.039	0.40	1.00
b1	0.046	0.070	1.17	1.78
c	0.013	0.026	0.33	0.65
c1	0.045	0.057	1.15	1.45
D	0.382	0.417	9.70	10.60
E	0.335	0.374	8.50	9.50
e	0.094	0.104	2.40	2.65
F	0.100	0.134	2.54	3.40
L	0.500	0.579	12.70	14.70
L1	0.079	0.134	2.00	3.40

## 6. Part Marking System



## 7. Package Information

Package	Packing Type	Quantity(pcs)
TO-220	Tube	50



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